



America Semiconductor

Silicon Super Fast Recovery Diode

**MURT20040 thru
MURT20060R**

**V_{RRM} = 50 V - 600 V
I_F = 200 A**

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

Three Tower Package



Maximum ratings, at T_j = 25 °C, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MURT20040 (R)	MURT20060 (R)	Unit
Repetitive peak reverse voltage	V _{RRM}		400	600	V
RMS reverse voltage	V _{RMS}		283	424	V
DC blocking voltage	V _{DC}		400	600	V
Continuous forward current	I _F	T _C ≤ 140 °C	200	200	A
Surge non-repetitive forward current, Half Sine Wave	I _{F,SM}	T _C = 25 °C, t _p = 8.3 ms	2000	2000	A
Operating temperature	T _j		-40 to 175	-40 to 175	°C
Storage temperature	T _{stg}		-40 to 175	-40 to 175	°C

Electrical characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	MURT20040 (R)	MURT20060 (R)	Unit
Diode forward voltage	V _F	I _F = 100 A, T _j = 25 °C	1.35	1.7	V
Reverse current	I _R	V _R = 50 V, T _j = 25 °C	25	25	μA
		V _R = 50 V, T _j = 125 °C	1	1	mA
Recovery Time					
Maximum reverse recovery time	T _{RR}	I _F = 0.5 A, I _R = 1.0 A, I _{RR} = 0.25 A	90	160	nS
Thermal characteristics					
Thermal resistance, junction - case	R _{thJC}		0.18	0.18	°C/W





Figure .1- Typical Forward Characteristics

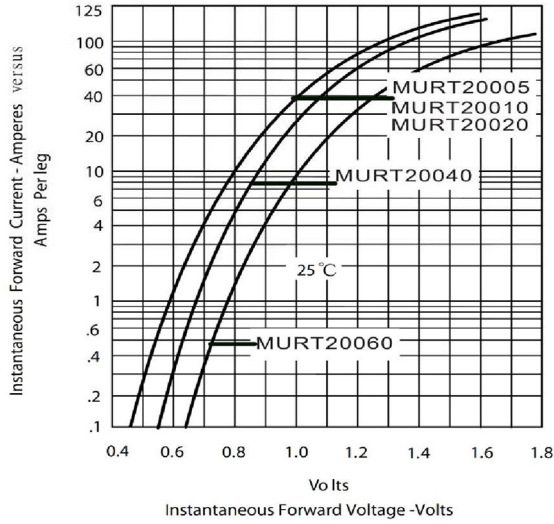


Figure .2- Forward Derating Curve

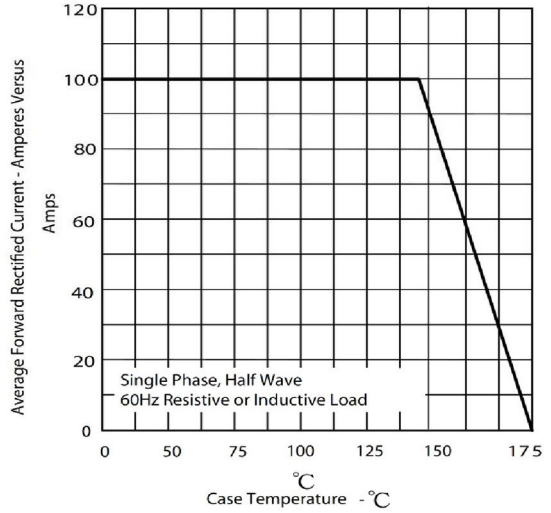


Figure.3- Peak Forward Surge Current

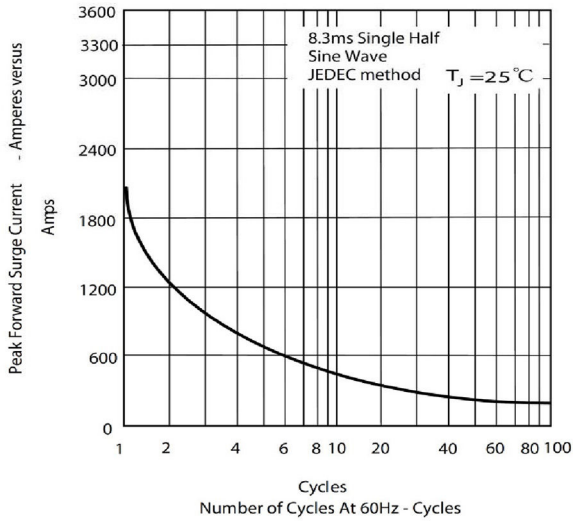


Figure.4- Typical Reverse Characteristics

